



SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET

2SK3746 — High-Voltage, High-Speed Switching Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- High reliability (Adoption of HVP process).
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		1500	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		2	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	4	A
Allowable Power Dissipation	P_D	$T_c = 25^\circ C$	2.5	W
			110	W
Channel Temperature	T_{ch}		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$
Avalanche Energy (Single Pulse) *1	E_{AS}		42	mJ
Avalanche Current *2	I_{AV}		2	A

*1 $V_{DD} = 99V$, $L = 20mH$, $I_{AV} = 2A$ *2 $L \leq 20mH$, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1mA$, $V_{GS} = 0V$	1500			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 1200V$, $V_{GS} = 0V$			100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16V$, $V_{DS} = 0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V$, $I_D = 1mA$	2.5		3.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 20V$, $I_D = 1A$	0.7	1.4		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D = 1A$, $V_{GS} = 10V$		10	13	Ω

Marking : K3746

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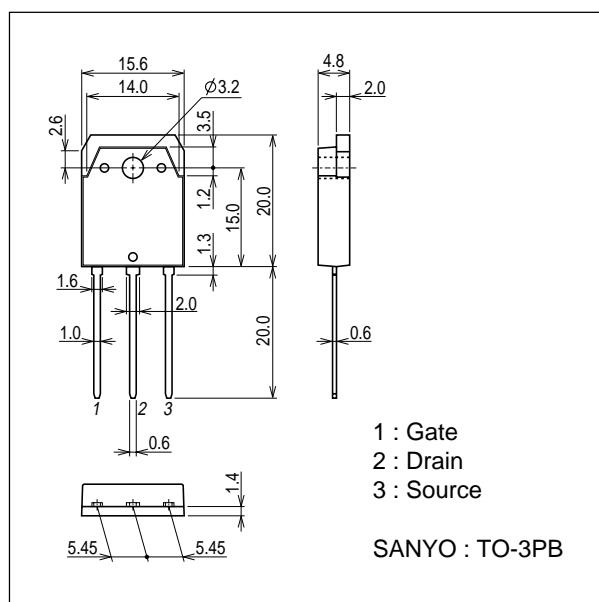
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	C_{iss}	$V_{DS}=30V, f=1MHz$		380		pF
Output Capacitance	C_{oss}	$V_{DS}=30V, f=1MHz$		70		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=30V, f=1MHz$		40		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		12		ns
Rise Time	t_r	See specified Test Circuit.		37		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		152		ns
Fall Time	t_f	See specified Test Circuit.		59		ns
Total Gate Charge	Q_g	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		37.5		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		2.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		20		nC
Diode Forward Voltage	V_{SD}	$I_S=2A, V_{GS}=0V$		0.88	1.2	V

Note) Although the protection diode is contained between gate and source, be careful of handling enough.

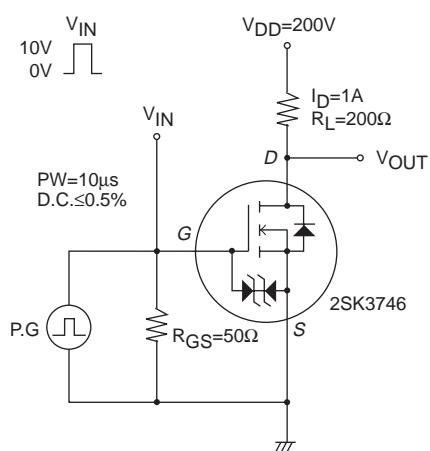
Package Dimensions

unit : mm

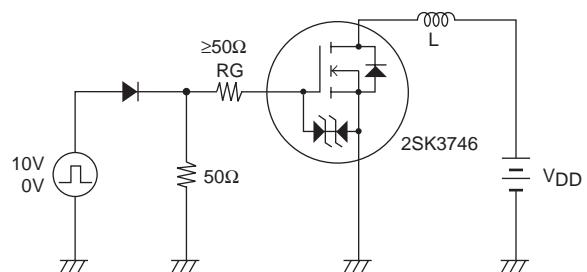
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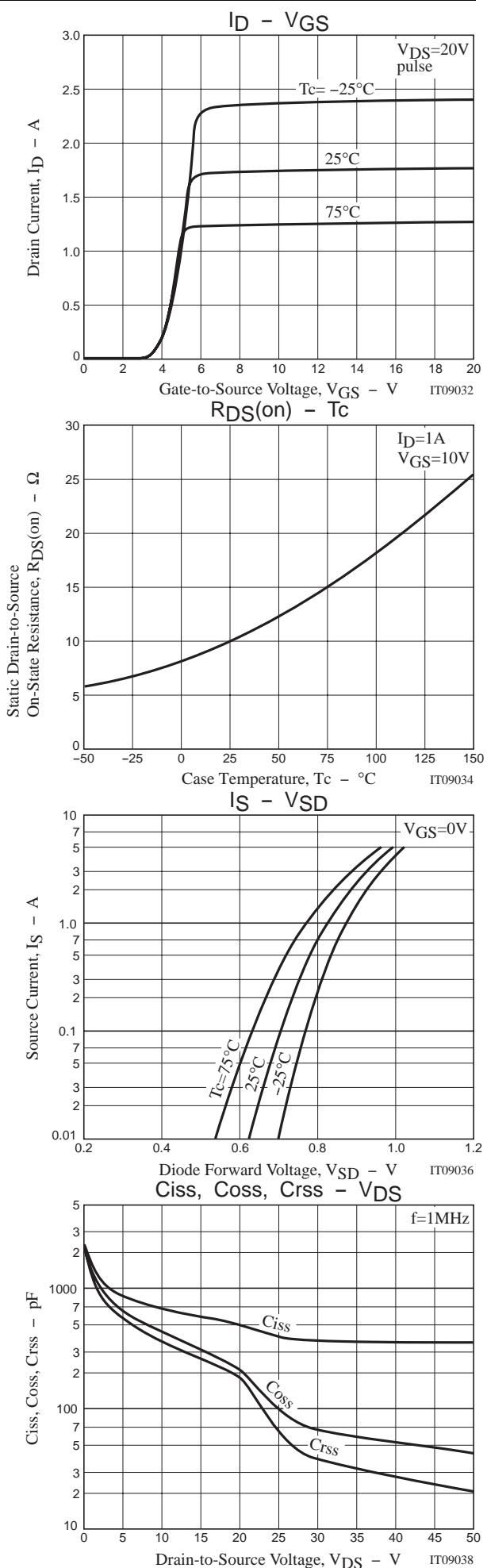
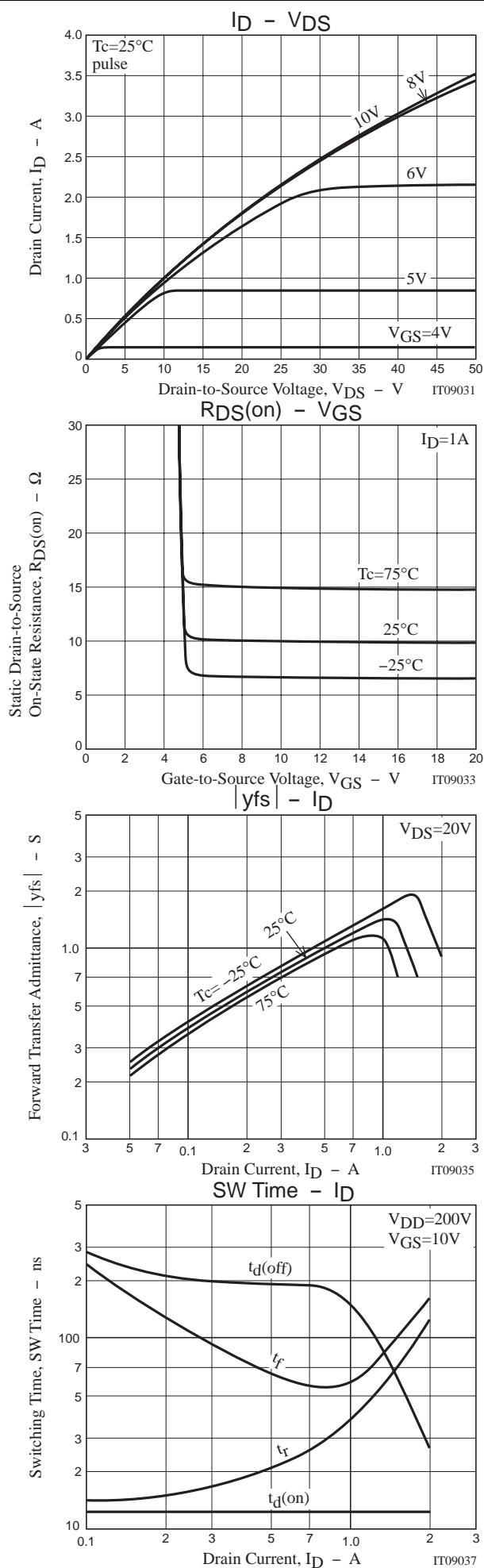


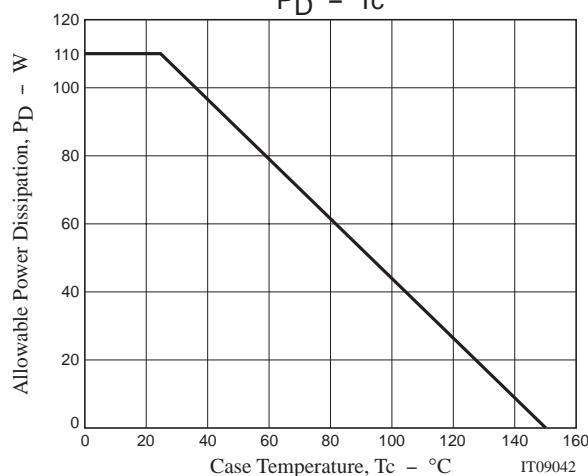
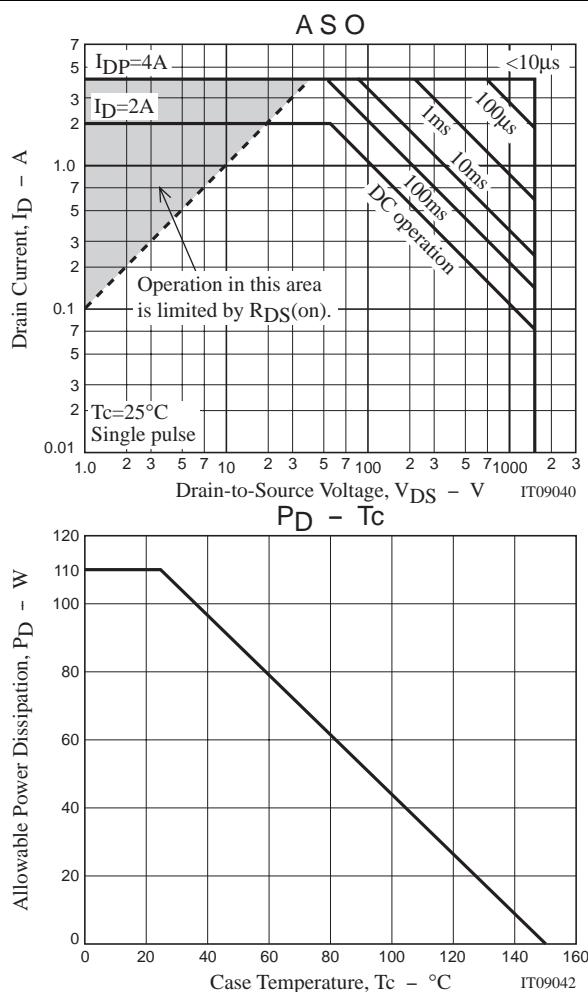
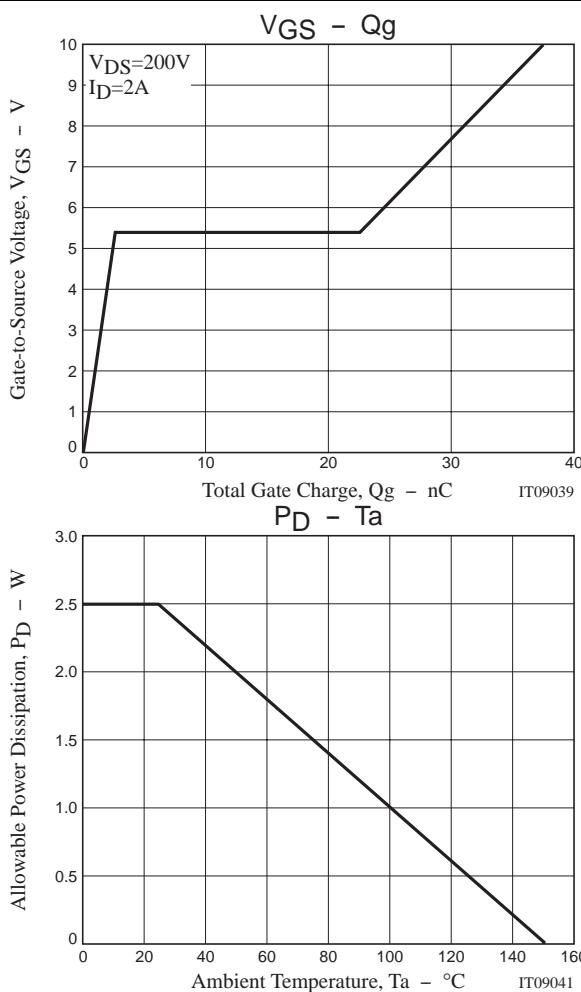
Switching Time Test Circuit



Avalanche Resistance Test Circuit







Note on usage : Since the 2SK3746 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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